ABSTRACT OF THE DISCLOSURE

A near-hermetic microwave semiconductor device, suitable for wideband high frequency applications including Phased Array Antenna systems, includes a PWB as a substrate; a GaAs Monolithic Microwave Integrated Circuit (MMIC) disposed on the substrate; a silicon carbide sealant disposed on the MMIC; and a Backside Interconnect with solder attachment which connects the substrate to the silicon carbide-coated MMIC. A conformal coating is disposed on the sealant, and a cover is disposed on the conformally-coated MMIC.

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